

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0049] as follows:

[0049] The thin film transistor (TFT) may be formed in a “L” or “U” shape, as shown in FIG. 3A and FIG. 3B, respectively. If the channel of the TFT is formed in an “L” or “U” shape, it is possible to improve the aperture ratio and reduce parasitic capacitance between the gate line and the drain electrode.

Please amend paragraph [0041] as follows:

[0041] Referring to FIGs. 6-8, an electric field inducing window may be formed in the pixel electrode 59 (60a), the passivation film 57 (60b) and/or the gate insulating film 55 (60c). The electric field inducing window may have a slit or hole ~~substantially circular~~ shape. For example, as shown in FIG. 6, the slit 60a is formed in the pixel electrode 59. FIG. 7 shows a hole 60b formed in the passivation film 57. FIG. 8 shows a hole 60b formed in the passivation film 57 and the gate insulating film 55.